

PCN# 20120418001<mark>C</mark> Transfer of select devices in the LBC4 process node to CFAB Facility Change Notification / Sample Request

Date:9/20/2016To:TOKYO ELECTRON DEVICE (DSTR) PCN

Dear Customer:

PCN Revision C is to announce the <u>retraction</u> of select devices.

In January, 2012, TI announced plans to close two older 6-inch manufacturing facilities in Hiji, Japan and Houston, Texas. Notification for transfer of devices will be distributed in phases, by technology, over the coming weeks. This product change announcement is to support transfer of products in the LBC4 process node from these wafer fabs to alternate sites. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days to ensure you can complete your evaluation and product transfer to the new site can be completed prior to the fab closure.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (<u>PCN_ww_admin_team@list.ti.com</u>).

Sincerely,

PCN Team SC Business Services

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE

TPS54610PWPR TPS54610PWP CUSTOMER PART NUMBER

null null

Technical details of this Product Change follow on the next page(s).

PCN Num	ber:	PCN2	0120418001	PCN Date: Sept. 20, 2016			016			
Title: Transfer of select devices in the LBC4 process node to CFAB Facility							ility			
Custome	r Contact:	PCN	Manager	Dept:			Quality Services			
Proposed 1 st Ship Date: April 20		April 2013		Estimated S Availability:		nple	Samples support is currently being coordinated.			
Change T	ype:		•							
Asse	Assembly Site Asser		Assembly F	bly Process			Assembly Materials			
Desig	jn		Electrical S	cal Specification			Mechanical Specification			
Test	Site		Packing/Sh	nipping	J/Labeling	<u> </u>	Test Process			
Wafe	r Bump Site		Wafer Bum	ip Mat	erial	<u> </u>	Wafer Bu	mp Process		
	r Fab Site		water Fab	Materi DCN			water Fa	D Process		
Descripti	on of Chang			PCN	Details					
The purpo	on of Chang	je: ovicio	n C is to ann	ounco	the retract	ion	of select d	avices Petracted		
devices are identified with a strikethrough and are highlighted in yellow in the Product Affected Section. These devices will remain at the current Fab Site. This change notification is to announce the transfer of select devices in the LBC4 process node from HFAB and HIJI to the CFAB (Chengdu, China) facility. These devices are listed in "Product Affected" section.										
Current			Nev	N						
Sites, Pro	ocess, Wafer	Diame	ter Site	Site, Process, Wafer Diameter						
HFAB/HIJI	/HU-BUMP, LE	3C4, 15	0mm CFA	B/Cla	rk-Bump/DE	BUMI	P, LBC4, 20)0mm		
 Device Groups in Product Affected Section Group 1: Devices with Fab Transfer and Bump site change to Clark-Bump/DBUMP Group 2: Devices with Fab Transfer Only *Proposed 1st Ship Date is based on current Qual Schedule. Bump sites were previously qualified. Reference quals are provided in the Qual Data Section 										
Reason for Change:										
Continuity	Continuity of Supply. HIJI/HFAB site shutdown.									
Anticipat	ed impact o	n For	m, Fit, Func	tion, (Quality or F	lelia	bility (po	sitive / negative):		
None										
Changes to product identification resulting from this PCN:										
Current										
Chip Site		Chip	site code (20	L) C	Chip country coo		e (21L)			
HU-BIP-4		HOU		USA						
HIJI		HIJ		JPN						
New										
Chip Site	8	Chip (20L	site code)	C (hip country 21L)		de			
C	FAB		CU3		СН	Ν				
				.						

Sample product shipping label (not actual product label)							
TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 2Q: MSL 2/260C/1 YEAR SEAL DT MSL 1/235C/UNLIM 03/29/04 OPT: ITEM: 39 LBL: 5A (L)T0:1750		(1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483S12 (P) (2P) REV: (V) 0033317 (20L) CS0: SHE (21L) CC0:USA (22L) ASO: MLA (23L) ASO: MYS					

Product Affected:						
Group 1: Devices wit	h Fab Transfer and Bump	site change				
HPA00182DDAR	TLC5947RHBR	TPS2062ADG4	TPS54610PWP			
HPA00295DDAR	TLC5947RHBRG4	TPS2062ADR	TPS54610PWPG4			
HPA00393DDAR	TLC5947RHBT	TPS2062ADRBR	TPS54610PWPR			
HPA00534DBQR	TLC5947RHBTG4	TPS2062ADRBRG4	TPS54610PWPRG4			
HPA00596BDR	TLC5951DAP	TPS2062ADRBT	TPS54611PWP			
HPA00638DAPR	TLC5951DAPR	TPS2062ADRBTG4	TPS54611PWPG4			
HPA00796PWPR	TLC5951RHAR	TPS2062ADRG4	TPS54611PWPR			
HPA01116RHBR	TLC5951RHAT	TPS2062D	TPS54611PWPRG4			
SN0809080DAPR	TLC5952DAP	TPS2062DG4	TPS54612PWP			
SN1002018DAPR	TLC5952DAPR	TPS2062DGN	TPS54612PWPG4			
SN105116PWP	TLC5970RHPR	TPS2062DGNG4	TPS54612PWPR			
SN105116PWPG4	TLC5970RHPT	TPS2062DGNR	TPS54612PWPRG4			
SN105116PWPR	TLC59711PWP	TPS2062DGNRG4	TPS54613PWP			
SN105116PWPRG4	TLC59711PWPR	TPS2062DR	TPS54613PWPG4			
SN1107015PWPR	TLC5971PWP	TPS2062DRG4	TPS54613PWPR			
TLC59281DBQ	TLC5971PWPR	TPS2064DGN	TPS54613PWPRG4			
TLC59281DBQR	TLC5971RGER	TPS2064DGNG4	TPS54614PWP			
TLC59281RGER	TLC5971RGET	TPS2064DGNR	TPS54614PWPG4			
TLC59281RGET	TPS2042BD	TPS2064DGNRG4	TPS54614PWPR			
TLC59282DBQ	TPS2042BDG4	TPS2064DRBR	TPS54614PWPRG4			
TLC59282DBQR	TPS2042BDGN	TPS2064DRBT	TPS54615PWP			
TLC59282RGER	TPS2042BDGNG4	TPS2066AD	TPS54615PWPG4			
TLC59282RGET	TPS2042BDGNR	TPS2066ADG4	TPS54615PWPR			
TLC5928DBQ	TPS2042BDGNRG4	TPS2066ADR	TPS54615PWPRG4			
TLC5928DBQG4	TPS2042BDR	TPS2066ADRBR	TPS54616PWP			
TLC5928DBQR	TPS2042BDRBR	TPS2066ADRBRG4	TPS54616PWPG4			
TLC5928DBQRG4	TPS2042BDRBT	TPS2066ADRBT	TPS54616PWPR			
TLC5928PW	TPS2042BDRG4	TPS2066ADRBTG4	TPS54616PWPRG4			
TLC5928PWG4	TPS2052BD	TPS2066ADRG4	TPS54810PWP			
TLC5928PWP	TPS2052BDG4	TPS2066D	TPS54810PWPG4			
TLC5928PWPG4	TPS2052BDGN	TPS2066DG4	TPS54810PWPR			
TLC5928PWPR	TPS2052BDGNG4	TPS2066DGN	TPS54810PWPRG4			
TLC5928PWPRG4	TPS2052BDGNR	TPS2066DGNG4	TPS65563ARGTR			
TLC5928PWR	TPS2052BDGNRG4	TPS2066DGNR	TPS65563ARGTRG4			
TLC5928PWRG4	TPS2052BDR	TPS2066DGNRG4	TPS65563ARGTT			
TLC5928RGER	TPS2052BDRBR	TPS2066DR	TPS65563ARGTTG4			
TLC5928RGET	TPS2052BDRBT	TPS2066DRG4	TPS65563RGTR			
TLC5944PWP	TPS2052BDRG4	TPS5430DDA	TPS65563RGTRG4			
TLC5944PWPG4	TPS2060DGN	TPS5430DDAG4	TPS65563RGTT			
TLC5944PWPR	TPS2060DGNG4	TPS5430DDAR	TPS65563RGTTG4			
TLC5944PWPRG4	TPS2060DGNR	TPS5430DDARG4	TPS65573DSSR			

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TLC5944RHBR	TPS2060DGNRG4	TPS5431DDA	TPS65573DSST
TLC5944RHBRG4 TPS2060DRBR		TPS5431DDAG4	
TLC5944RHBT TPS2060DRBT		TPS5431DDAR	
TLC5944RHBTG4 TPS2062AD		TPS5431DDARG4	
Group 2: Devices with	h Fab Transfer Only		
SN0707071PWR	TPS53124PWR	TPS53125RGER	TPS53127RGET
SN0707071PWRG4	TPS53124PWRG4	TPS53125RGET	TPS53128PW
SN0911044PWR	TPS53124RGER	TPS53126PW	TPS53128PWR
TPS53114APW	TPS53124RGERG4	TPS53126PWR	TPS53128RGER
TPS53114APWR	TPS53124RGET	TPS53126RGER	TPS53128RGET
TPS53114PW	TPS53124RGETG4	TPS53126RGET	TPS53129PW
TPS53114PWR	TPS53125PW	TPS53127PW	TPS53129PWR
TPS53124PW	TPS53125PWR	TPS53127PWR	TPS53129RGER
TPS53124PWG4	TPS53125PWR-SH	TPS53127RGER	TPS53129RGET

Qualification Plan:								
This qualification has been developed for the validation of this change. The qualification data will								
validate that the proposed cl	validate that the proposed change meets the applicable released technical specifications.							
Qualification Schedule:		Start:	February 2	2013	End:	April 2	013	
Qual V	ehicle	1: TPS5	4610PWP	(MSL Le	vel 2-26	50C)		
Wafer Fab Site: CFAB		Metallization: TiW/AlSiCu.5%						
Wafer Fab Process: LBC4		Waf	er Diameter:	200 mr	n			
Qualification: 🛛 Plan	Τε	est Resul	ts					
Reliability Test	0	nditions				Sam	ple Size,	/Fails
		nuncions				Lot#1	Lot#2	Lot#3
Preconditioning	(le	vel 2 @ 2	60C peak +	5/-0C)		385/0	385/0	385/0
HTOL High Temp Op Life	12	125C (1000 Hrs)			77/0	77/0	77/0	
Electrical Characterization					30/0	30/0	30/0	
**High Temp. Storage Bake		170C (420 Hrs)			77/0	77/0	77/0	
**Biased HAST		130C/85%RH (96 Hrs)			77/0	77/0	77/0	
**Autoclave		121C (96 Hrs)			77/0	77/0	77/0	
**T/C -65C/150C		-65C/+150C (500 Cycles)			77/0	77/0	77/0	
ESD CDM	50	500V			3/0	3/0	3/0	
ESD HBM	20	2000V			3/0	3/0	3/0	
Wafer Level Reliability		Approved by TDQRE			1/0	1/0	1/0	
Latch-Up		1.5xVcc\25C\250mA			6/0	6/0	6/0	
Manufacturability (Assembly)		(per mfg. Site specification)			1/0	1/0	1/0	
Manufacturability (Wafer Fab)		(per mfg. Site specification)			1/0	1/0	1/0	
Moisture Level Sensitivity	Le	Level 2 @ 260C +5/-0C			12/0	-	-	
**Preconditioning: Level 2-260C								

Reference Quals

DBUMP Facility Qualification for the copper processing on the Cu/BOAC/COA								
Qualification Data: (Approved: 10/31/2003)								
This qualification has	This qualification has been developed for the validation of this change. The qualification data will							
validate that the proposed change meets the applicable released technical specifications.								
Qual Vehicle: SH6950DAA0PFP (MSL Level 1–235C)								
Wafer Fab Site:	DFAB		Metallization:	TiW/AlSiCu.5	%			
Wafer Fab Process:	LBC4		Wafer Diameter:	200mm				
Passivation 4KAOX/8KACN								
Qualification:	Plan	🖂 Te	st Results		1			
Reliability Test		Condit	tions		Sample Size/Fails Lot#1 Lot#2 Lot#3			
**Life Test		125C	(1000 hrs)		77/0	77/0	77/0	
**Autoclave		121C,	15 PSIG (240 hrs)		77/0	77/0	77/0	
**Temp Cycle		-65/+	150C (500 Cycles)		77/0	77/0	77/0	
**Thermal Shock		-65/+	150C (500 Cycles)		77/0	77/0	77/0	
Manufacturability (Asse	embly)	(per m	fg. Site specification)		Approved	-	-	
**Preconditioning: L	evel 3-2	260C						
Clark BOAC facility Qualification for 10um thick BOAC								
Qualification Data: (Approved: 10/26/2010)								
This qualification has been developed for the validation of this change. The qualification data will								
validate that the proposed change meets the applicable released technical specifications.								
Qual Vehicle 1: SH6966ACCORGC (MSL Level 3-260C)								
Wafer Fab Site: MIHO8		8	Metallization:	AlCu				
Wafer Fab Process: LBC7			water Diameter: 200mm					
Bump Site: Clark								
Reliability Test			Conditions	Lot#1 Lot#2 Lot#3				
**Autoclave			121C (96 hrs)	77/0	77/0	77/0		
**Biased HAST			130C/85%RH (96 hrs	40/0	77/0	40/0		
**High Temp. Storage	Bake		170C (420 Hrs)	77/0	77/0	77/0		
**Temp Cycle			-65/+150C (500 Cyc	82/0	82/0	81/0		
**Thermal Shock			-65/+150C (500 Cyc	77/0	77/0	77/0		
Backgrind Characterizaton			-	Pass	Pass	Pass		
Ball Bond Shear			Wires	76/0	76/0	76/0		
Bond Pull			Wires	76/0	76/0	76/0		
Die Shear			-		10/0	10/0	10/0	
Electrical Characterizat	ion		-		Pass	-	_	
Manufacturability (Asse	mbly)		(per mfg. Site specifica	tion)	Approved	-	_	
Moisture Sensitivity,	JEDEC		Level 3-260C	22/0	22/0	22/0		
**Preconditioning: Level 3-260C								

	Qual Vehicle	2: TPS65852ZQZ	(MSL Level 3-2	260C)		
Wafer Fab Site: MIHO8		Metallization:	AlCu			
Wafer Fab Process: LBC7		Wafer Diameter:	200mm			
Bump Site: Clark						
Qualification: 🗌 Plan 🛛 Test Results						
Reliability Test		Conditions		Sample Size/Fails		
				Lot#1	Lot#2	Lot#3
**Temperature Cycle		-55/125C (500 Cycles)		77/0	-	-
Ball Bond Shear		Wires		76/0	76/0	76/0
Bond Pull		Wires		76/0	76/0	76/0
Manufacturability (Asse	embly)	(per mfg. Site specification)		Approved	-	-
**Preconditioning: Level 3-260C						

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com